

TPR 175

175 Watts, 50 Volts, Pulsed Avionics 1030 - 1090 MHz

GENERAL DESCRIPTION

The TPR 175 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 1030-1090 MHz. The device has gold thin-film metallization for proven highest MTTF. The transistor includes input prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C² 388 Watts

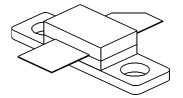
Maximum Voltage and Current

BVces Collector to Base Voltage 55 Volts
BVebo Emitter to Base Voltage 3.5 Volts
Ic Collector Current 12.5 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 150^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$

CASE OUTLINE 55CX, STYLE 1



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg η _c VSWR	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	F = 1090 MHz Vcc = 50 Volts PW = 10 μsec DF = 1% F = 1090 MHz	175 8.0	9.0 40	25	Watts Watts dB %

BVebo BVces	Emitter to Base Breakdown Collector to Emitter Breakdown	Ie = 5 mA $Ic = 20 mA$	3.5 55		Volts Volts
$rac{\mathbf{h_{FE}}}{\mathbf{ heta jc}^2}$	DC - Current Gain Thermal Resistance	Ic = 20 mA, Vce = 5V	10	0.45	°C/W

Note 1: At rated output power and pulse conditions

2: At rated pulse conditions

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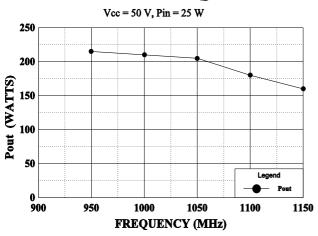
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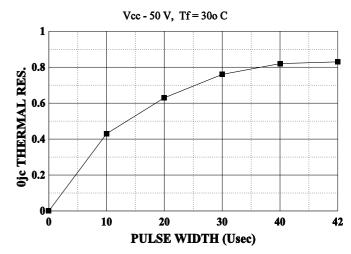


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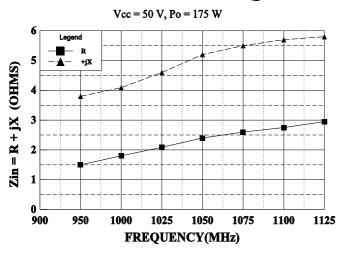
POWER OUTPUT vs FREQUENCY



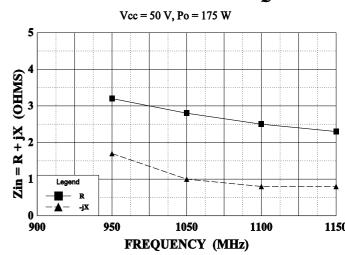
THERMAL RESISTANCE vs PULSE WIDTH

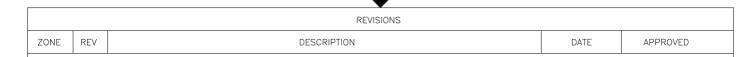


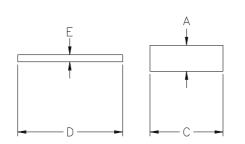
SERIES INPUT IMPEDANCE vs FREQUENCY

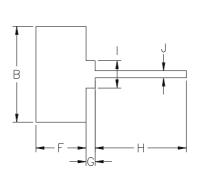


SERIES LOAD IMPEDANCE vs FREQUENCY



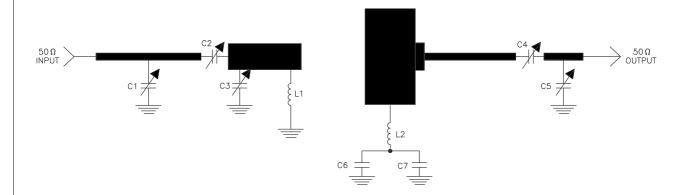






DIM	INCHES	
Α	.285	
В	1.050	
С	.800	
D	1.150	
Е	.078	
F	.550	
G	.100	
Н	1.000	
1	.300	
J	.078	

1030/1090 TEST AMPLIFIER



Material 1/32" Teflon Fiberglass C1,C3,C5 = .3-3.5 Johanson C2,C4 = .6-6 Johanson C6 = 82pf A.T.C. C7 = 200 μ f Electrolytic

 $C7 = 200\mu f$ Electrolytic $L1 = \#18 \text{ AWG } 0.6^{\circ} \text{ LONG}$ $L2 = \#18 \text{ AWG } 1.0^{\circ} \text{ LONG}$



cage OPJR2	DWG NO.	TPR 175		REV A
	SCALE	1/1	SHEET	